



FEATURES

- Access time : 35/70ns (max.)
- Low power consumption:
 Operating : 40 mA (typical.)
 Standby : 3mA (typical) normal
 2uA (typical) L-version
 1uA (typical) LL-version
- Single 5V power supply
- All inputs and outputs are TTL compatible
- Fully static operation
- Three state outputs
- Data retention voltage : 2V (min.)
- Package : 28-pin 600 mil PDIP
 28-pin 330 mil SOP
 28-pin 8mmx13.4mm STSOP

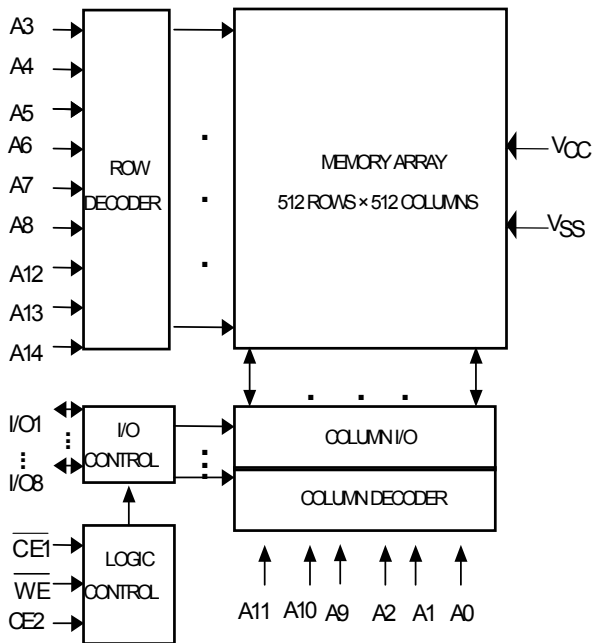
GENERAL DESCRIPTION

The UT62257C is a 262,144-bit low power CMOS static random access memory organized as 32,768 words by 8 bits. It is fabricated using high performance, high reliability CMOS technology.

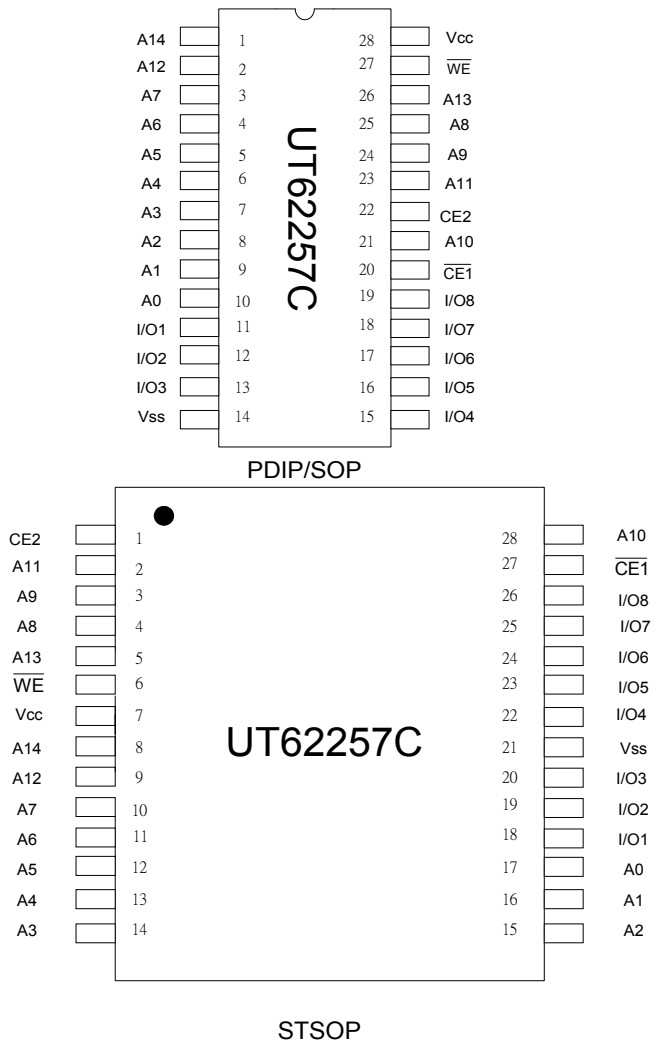
The UT62257C is designed for high-speed and low power application. With 2 chip controls ($\overline{CE1}$ - CE2), it is easy to design memory systems with POWER-DOWN and capacity expansion in the application circuits. It is particularly well suited for battery back-up nonvolatile memory application.

The UT62257C operates from a single 5V power supply and all inputs and outputs are fully TTL compatible.

FUNCTIONAL BLOCK DIAGRAM



PIN CONFIGURATION



PIN DESCRIPTION

SYMBOL	DESCRIPTION
A0 - A14	Address Inputs
I/O1 - I/O8	Data Inputs/Outputs
$\overline{CE1}$ - CE2	Chip Enable Inputs
\overline{WE}	Write Enable Input
V _{cc}	Power Supply
V _{ss}	Ground



ABSOLUTE MAXIMUM RATINGS*

PARAMETER	SYMBOL	RATING	UNIT
Terminal Voltage with Respect to V _{SS}	V _{TERM}	-0.5 to +7.0	V
Operating Temperature	T _A	0 to +70	°C
Storage Temperature	T _{STG}	-65 to +150	°C
Power Dissipation	P _D	1	W
DC Output Current	I _{OUT}	50	mA
Soldering Temperature (under 10 sec)	T _{solder}	260	°C

*Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to the absolute maximum rating conditions for extended period may affect device reliability.

TRUTH TABLE

MODE	CE1	CE2	WE	I/O OPERATION	SUPPLY CURRENT
Standby	H	X	X	High - Z	I _{SB} , I _{SB1}
	X	L	X	High - Z	I _{SB} , I _{SB1}
Read	L	H	H	D _{OUT}	I _{CC} , I _{CC1} , I _{CC2}
Write	L	H	L	D _{IN}	I _{CC} , I _{CC1} , I _{CC2}

Note: H = VIH, L=VIL, X = Don't care.

DC ELECTRICAL CHARACTERISTICS (V_{CC} = 5V±10%, TA = 0°C to 70°C)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Input High Voltage	V _{IH}		2.2	-	V _{CC} +0.5	V	
Input Low Voltage	V _{IL}		- 0.5	-	0.8	V	
Input Leakage Current	I _{LI}	V _{SS} ≤ V _{IN} ≤ V _{CC}	- 1	-	1	μA	
Output Leakage Current	I _{LO}	V _{SS} ≤ V _{I/O} ≤ V _{CC} CE1=V _{IH} or CE2 = V _{IL}	- 1	-	1	μA	
Output High Voltage	V _{OH}	I _{OH} = - 1mA	2.4	-	-	V	
Output Low Voltage	V _{OL}	I _{OL} = 4mA	-	-	0.4	V	
Operating Power Supply Current	I _{CC}	Cycle time=Min., I _{I/O} = 0mA , CE1 = V _{IL} , CE2 = V _{IH}	- 35	-	40	50	mA
			- 70	-	30	40	mA
	I _{CC1}	Cycle time=1μs, 100%duty, I _{I/O} =0mA, CE1 = 0.2V ; CE2 = V _{CC} -0.2V , other pins at 0.2V or V _{CC} -0.2V	-	-	10	mA	
I _{CC2}	Cycle time=500ns, 100%duty, I _{I/O} =0mA, CE1 = 0.2V ; CE2 = V _{CC} -0.2V , other pins at 0.2V or V _{CC} -0.2V	-	-	20	mA		
Standby Power Supply Current	I _{SB}	CE1=V _{IH} or CE2 = V _{IL}	normal	-	1	10	mA
				CE1 ≥ V _{CC} -0.2V CE2 ≥ V _{CC} -0.2V	0.3	5	mA
	I _{SB1}	CE1=V _{IH} or CE2 = V _{IL}	-L/-LL	-	-	3	mA
			CE1 ≥ V _{CC} -0.2V CE2 ≥ V _{CC} -0.2V	-L	-	2	100
			-LL	-	1	40	μA

**CAPACITANCE** (TA=25°C, f=1.0MHz)

PARAMETER	SYMBOL	MIN.	MAX	UNIT
Input Capacitance	C _{IN}	-	8	pF
Input/Output Capacitance	C _{I/O}	-	10	pF

Note : These parameters are guaranteed by device characterization, but not production tested.

AC TEST CONDITIONS

Input Pulse Levels	0V to 3.0V
Input Rise and Fall Times	5ns
Input and Output Timing Reference Levels	1.5V
Output Load	C _L = 100pF, I _{OH} /I _{OL} = -1mA/4mA

AC ELECTRICAL CHARACTERISTICS (V_{CC} = 5V±10% , TA = 0°C to 70°C)**(1) READ CYCLE**

PARAMETER	SYMBOL	UT62257C-35		UT62257C-70		UNIT
		MIN.	MAX.	MIN.	MAX.	
Read Cycle Time	t _{RC}	35	-	70	-	ns
Address Access Time	t _{AA}	-	35	-	70	ns
Chip Enable Access Time	t _{ACE}	-	35	-	70	ns
Output Enable Access Time	t _{OE}	-	25	-	35	ns
Chip Enable to Output in Low Z	t _{CLZ*}	10	-	10	-	ns
Output Enable to Output in Low Z	t _{OLZ*}	5	-	5	-	ns
Chip Disable to Output in High Z	t _{CHZ*}	-	25	-	35	ns
Output Disable to Output in High Z	t _{OHZ*}	-	25	-	35	ns
Output Hold from Address Change	t _{OH}	5	-	5	-	ns

(2) WRITE CYCLE

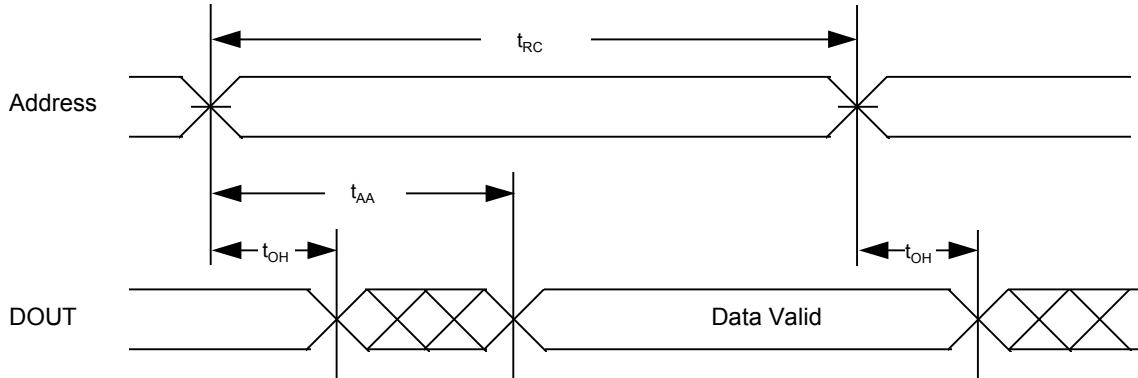
PARAMETER	SYMBOL	UT62257C-35		UT62257C-70		UNIT
		MIN.	MAX.	MIN.	MAX.	
Write Cycle Time	t _{WC}	35	-	70	-	ns
Address Valid to End of Write	t _{AW}	30	-	60	-	ns
Chip Enable to End of Write	t _{CW}	30	-	60	-	ns
Address Set-up Time	t _{AS}	0	-	0	-	ns
Write Pulse Width	t _{WP}	25	-	50	-	ns
Write Recovery Time	t _{WR}	0	-	0	-	ns
Data to Write Time Overlap	t _{DW}	20	-	30	-	ns
Data Hold from End of Write Time	t _{DH}	0	-	0	-	ns
Output Active from End of Write	t _{OW*}	5	-	5	-	ns
Write to Output in High Z	t _{WHZ*}	-	15	-	25	ns

*These parameters are guaranteed by device characterization, but not production tested.

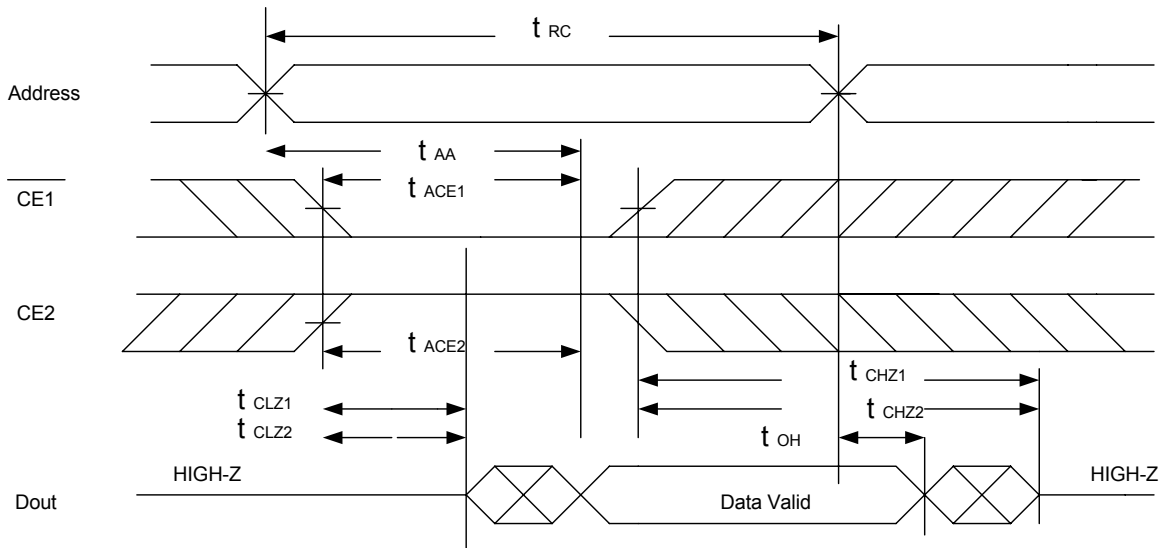


TIMING WAVEFORMS

READ CYCLE 1 (Address Controlled) (1,2,4)



READ CYCLE 2 ($\overline{CE1}$ and CE2 Controlled) (1,3,5,6)

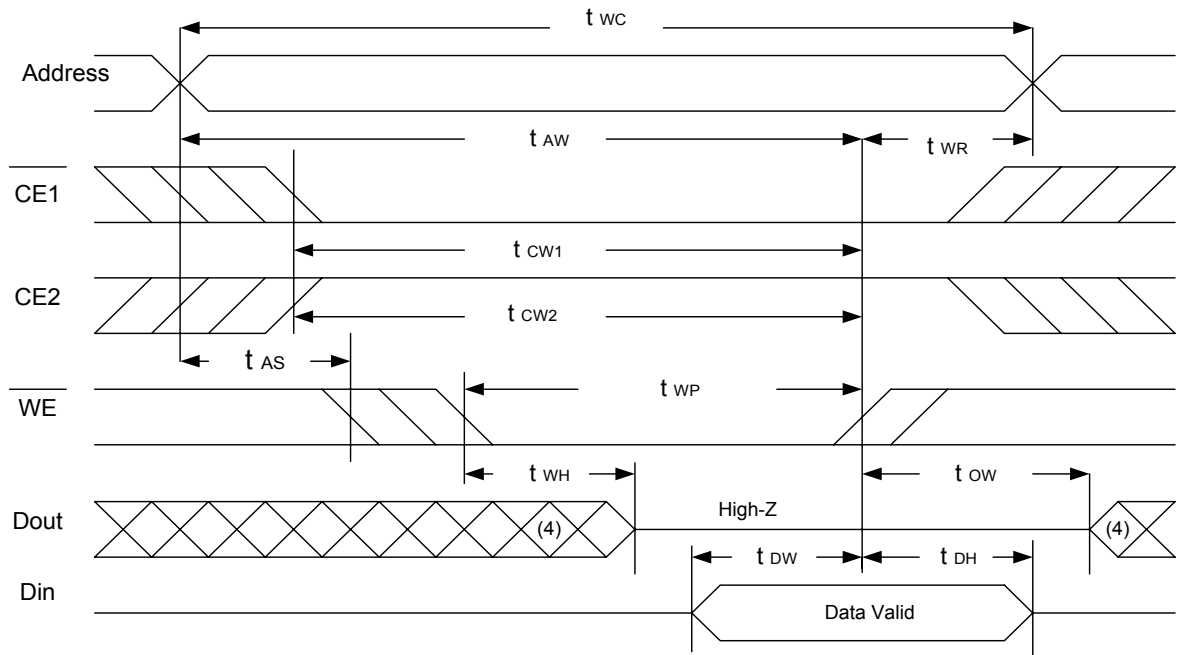


Notes :

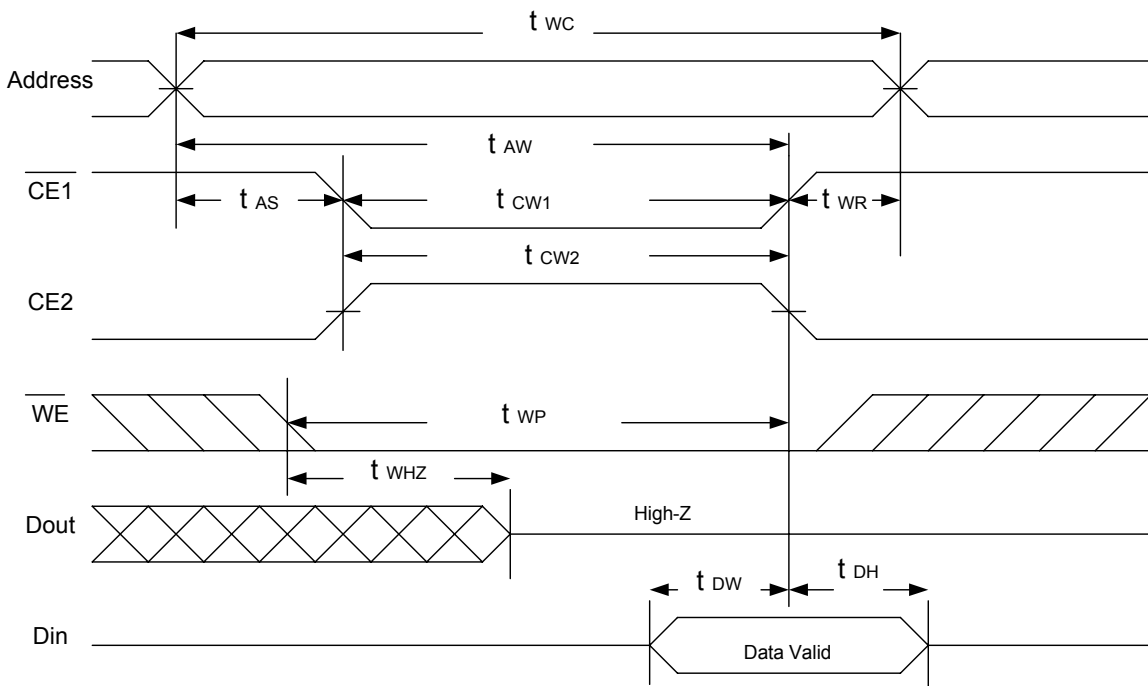
1. \overline{WE} is HIGH for read cycle.
2. Device is continuously selected $\overline{CE1} = V_{IL}$, $CE2 = V_{IH}$
3. Address must be valid prior to or coincident with $\overline{CE1}$, $CE2$ transition; otherwise t_{AA} is the limiting parameter.
5. t_{CLZ} , t_{OLZ} , t_{CHZ} and t_{OHZ} are specified with $CL = 5pF$. Transition is measured $\pm 50mV$ from steady state.
6. At any given temperature and voltage condition, t_{CHZ} is less than t_{CLZ} , t_{OHZ} is less than t_{OLZ} .



WRITE CYCLE 1 (\overline{WE} Controlled) (1,2,3,5)



WRITE CYCLE 2 ($\overline{CE1}$ and CE2 Controlled) (1,2,5)



Notes :

1. \overline{WE} or $\overline{CE1}$ must be high and CE2 must be low during all address transitions.
2. A write occurs during the overlap of a low $\overline{CE1}$ and a low \overline{WE} , and a high CE2.
3. During a \overline{WE} controlled with write cycle, t_{WP} must be greater than $t_{WHZ}+t_{DW}$ to allow the drivers to turn off and data to be placed on the bus.
4. During this period, I/O pins are in the output state, and input signals must not be applied.
5. If the $\overline{CE1}$ LOW transition occurs or CE2 high simultaneously with or after \overline{WE} LOW transition, the outputs remain in a high impedance state.
6. t_{OW} and t_{WHZ} are specified with $C_L = 5pF$. Transition is measured $\pm 500mV$ from steady state.

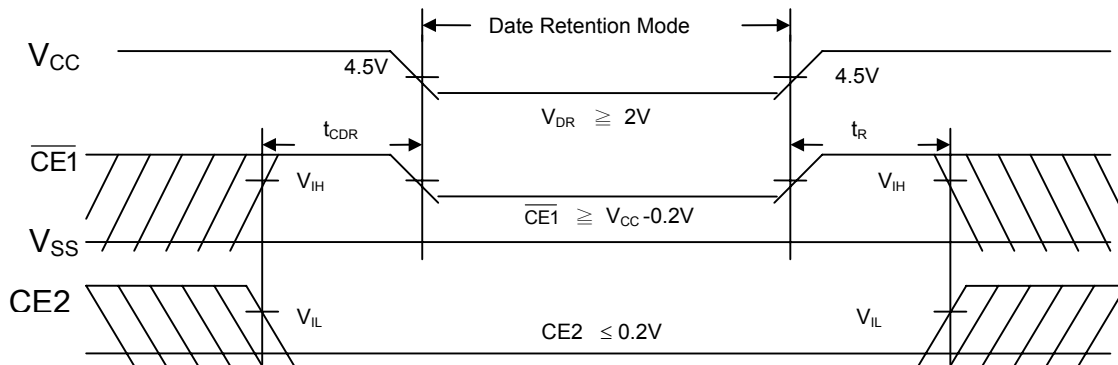


DATA RETENTION CHARACTERISTICS (TA = 0°C to 70°C)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Vcc for Data Retention	V_{DR}	$\overline{CE1} \geq V_{CC}-0.2V$ or $CE2 \leq 0.2V$	2.0	-	5.5	V	
Data Retention Current	I_{DR}	$V_{cc}=3V, CE2 \leq 0.2V$ or $\overline{CE1} \geq V_{CC}-0.2V$	- L	-	1	50	μA
			- LL	-	0.5	20	μA
Chip Disable to Data Retention Time	t_{CDR}	See Data Retention Waveforms (below)	0	-	-	ns	
Recovery Time	t_R		t_{RC}^*	-	-	ns	

t_{RC}^* = Read Cycle Time

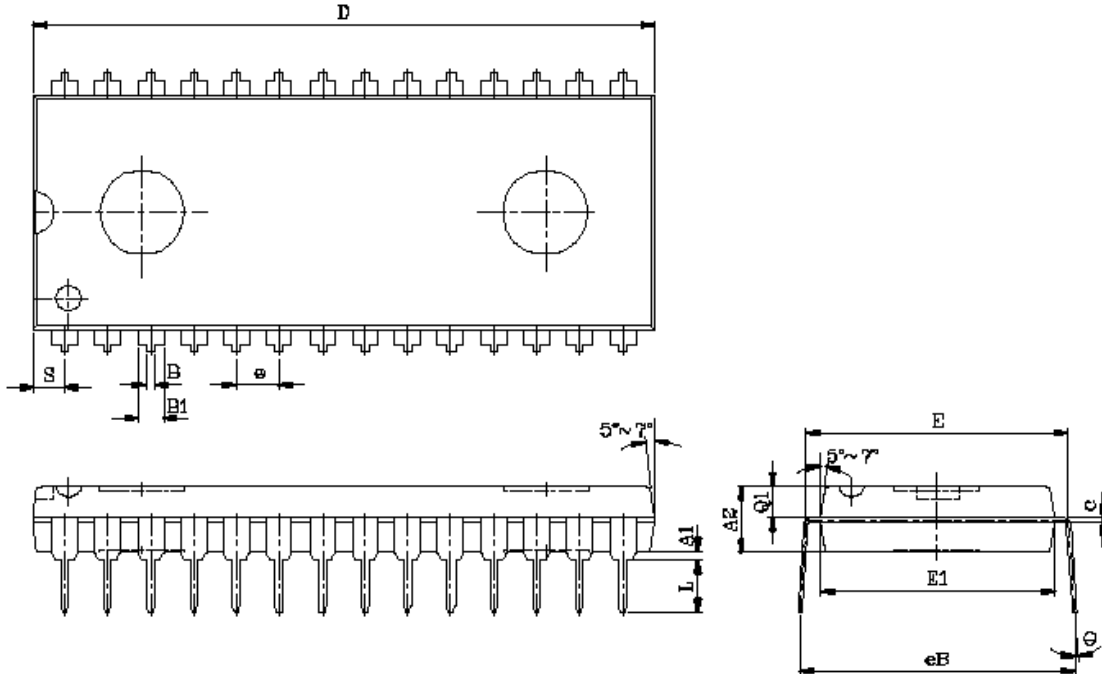
DATA RETENTION WAVEFORM





PACKAGE OUTLINE DIMENSION

28 pin 600 mil PDIP Package Outline Dimension



UNIT SYMBOL	INCH(BASE)	MM(REF)
A1	0.010 (MIN)	0.254 (MIN)
A2	0.150±0.005	3.810±0.127
B	0.020 (MAX)	0.508(MAX)
B1	0.055 (MAX)	1.397(MAX)
c	0.012 (MAX)	0.304 (MAX)
D	1.430 (MAX)	36.322 (MAX)
E	0.6 (TYP)	15.24 (TYP)
E1	0.52 (MAX)	13.208 (MAX)
e	0.100 (TYP)	2.540(TYP)
eB	0.625 (MAX)	15.87 (MAX)
L	0.180(MAX)	4.572(MAX)
S	0.06 (MAX)	1.524 (MAX)
Q1	0.08(MAX)	2.032(MAX)
θ	15°(MAX)	15°(MAX)



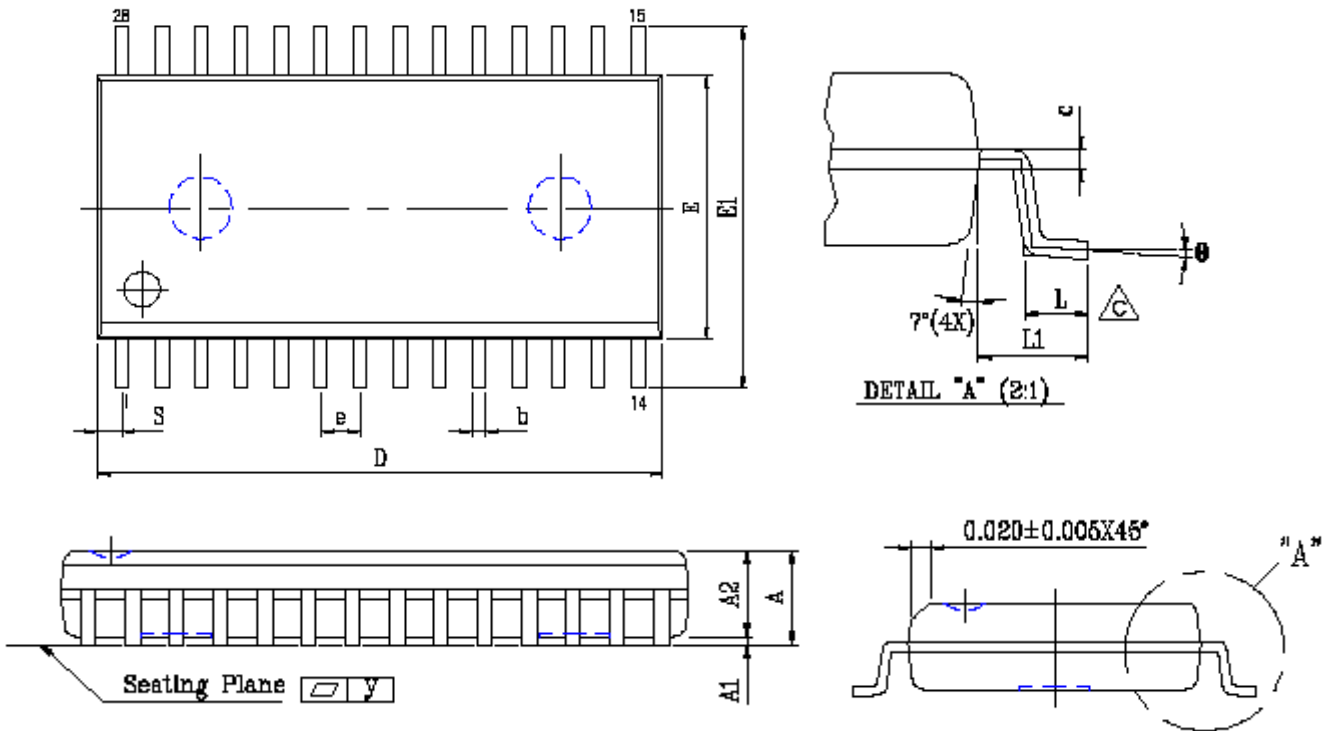
UTRON

Rev. 1.0

UT62257C

32K X 8 BIT LOW POWER CMOS SRAM

28 pin 330 mil SOP Package Outline Dimension



UNIT SYMBOL	INCH(BASE)	MM(REF)
A	0.120 (MAX)	3.048 (MAX)
A1	0.002(MIN)	0.05(MIN)
A2	0.098±0.005	2.489±0.127
b	0.0016 (TYP)	0.406(TYP)
c	0.010 (TYP)	0.254(TYP)
D	0.728 (MAX)	18.491 (MAX)
E	0.340 (MAX)	8.636 (MAX)
Δ_B E1	0.465±0.012	11.811±0.305
e	0.050 (TYP)	1.270(TYP)
Δ_C L	0.05 (MAX)	1.270 (MAX)
L1	0.067±0.008	1.702 ±0.203
S	0.047 (MAX)	1.194 (MAX)
Δ_E y	0.003(MAX)	0.076(MAX)
θ	0°~10°	0°~10°



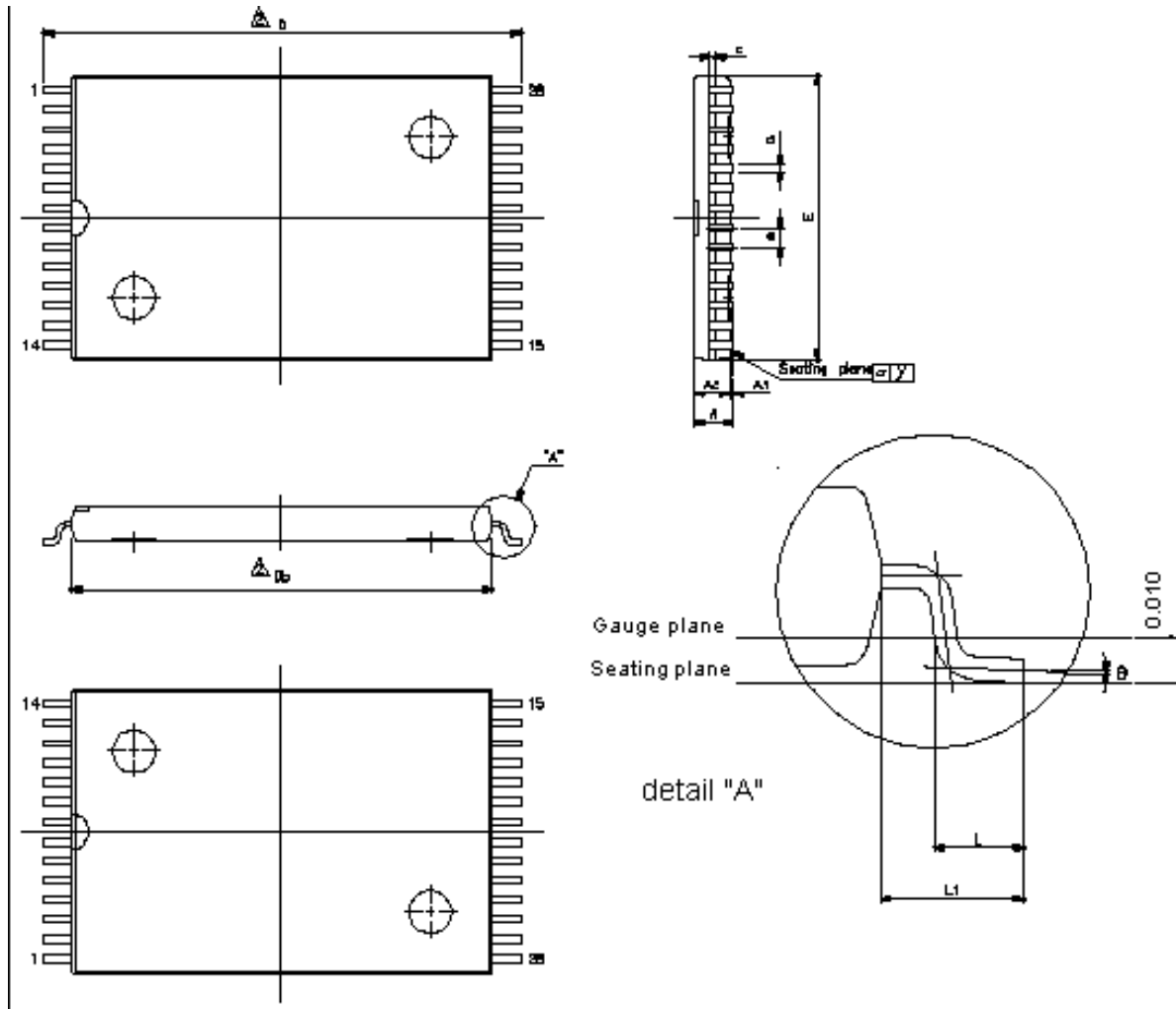
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Rev. 1.0

UT62257C

32K X 8 BIT LOW POWER CMOS SRAM

28 pin 8x13.4mm STSOP Package Outline Dimension



Note :
E dimension is not including end flash
the total of both sides' end flash is
not above 0.3mm.



UNIT SYMBOL	INCH(BASE)	MM(REF)
A	0.047 (MAX)	1.20 (MAX)
A1	0.004±0.002	0.10±0.05
A2	0.039±0.002	1.00±0.05
b	0.006 (TYP)	0.15(TYP)
c	0.010 (TYP)	0.254(TYP)
Db	0.465±0.004	11.80±0.10
E	0.315±0.004	8.00±0.10
e	0.022 (TYP)	0.55(TYP)
D	0.528±0.008	13.40±0.20
L	0.020±0.004	0.50±0.10
L1	0.0315±0.004	0.80±0.10
y	0.08(MAX)	0.003(MAX)
θ	0°~5°	0°~5°



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Rev. 1.0

UT62257C
32K X 8 BIT LOW POWER CMOS SRAM

ORDERING INFORMATION

PART NO.	ACCESS TIME (ns)	STANDBY CURRENT (μ A)	PACKAGE
UT62257CPC-70	70	5 mA	28 PIN PDIP
UT62257CPC-70L	70	100 μ A	28 PIN PDIP
UT62257CPC-70LL	70	40 μ A	28 PIN PDIP
UT62257CSC-35	35	5 mA	28 PIN SOP
UT62257CSC-35L	35	100 μ A	28 PIN SOP
UT62257CSC-35LL	35	40 μ A	28 PIN SOP
UT62257CSC-70	70	5 mA	28 PIN SOP
UT62257CSC-70L	70	100 μ A	28 PIN SOP
UT62257CSC-70LL	70	40 μ A	28 PIN SOP
UT62257CLS-35L	35	100 μ A	28 PIN STSOP
UT62257CLS-35LL	35	50 μ A	28 PIN STSOP
UT62257CLS-70L	70	100 μ A	28 PIN STSOP
UT62257CLS-70LL	70	40 μ A	28 PIN STSOP



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UT62257C

Rev. 1.0

32K X 8 BIT LOW POWER CMOS SRAM

REVISION HISTORY

REVISION	DESCRIPTION	DATE
Preliminary Rev. 0.1	Original.	Jun 7,2001
Rev. 1.0	1. TRUTH TABLE 2. DC ELECTRICAL CHARACTERISTICS	Jul 19,2001



Rev. 1.0

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32K X 8 BIT LOW POWER CMOS SRAM

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